

IRFM150 (JANTX2N7224)

PD-90487D

Repetitive Avalanche and dv/dt Rated Power MOSFET Thru-Hole (TO-254AA) 100V, 34A, N-channel, HEXFET™ MOSFET Technology

Features

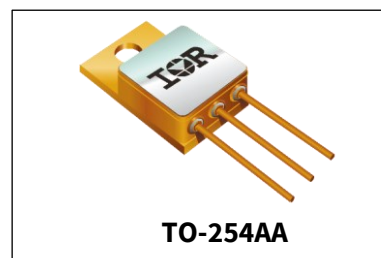
- Repetitive avalanche rating
- Hermetically sealed
- Electrically isolated
- Alternative to TO-3 Package
- Simple drive requirements
- Ceramic eyelets

Potential Applications

- DC-DC converter
- Motor drives

Product Summary

- **BV_{DS}** : 100V
- **I_D** : 34A
- **$R_{DS(on),max}$** : 70m Ω
- **$Q_{G,max}$** : 125nC
- **REF**: MIL-PRF-19500/592



Product Validation

Qualified to JANTXV screening flow according to MIL-PRF-19500 for high-reliability applications

Description

IR HiRel HEXFET™ technology is advanced line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high transconductance. HEXFET™ transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, fast switching and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, high energy pulse circuits, and virtually any application where high reliability is required. The HEXFET™ transistor's totally isolated package eliminates the need for additional isolating material between the device and the heatsink. This improves thermal efficiency and reduces drain capacitance.

Ordering Information

Table 1 **Ordering options**

Part number	Package	Screening Level
IRFM150	TO-254AA	COTS
JANTX2N7224	TO-254AA	JANTX
JANTXV2N7224	TO-254AA	JANTXV

IRFM150 (JANTX2N7224)

Power MOSFET Thru - Hole (TO-254AA)

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Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
$I_{D1} @ V_{GS} = 10V, T_C = 25^{\circ}C$	Continuous Drain Current	34	A
$I_{D2} @ V_{GS} = 10V, T_C = 100^{\circ}C$	Continuous Drain Current	21	A
$I_{DM} @ T_C = 25^{\circ}C$	Pulsed Drain Current ¹	136	A
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	150	W
	Linear Derating Factor	1.2	W/ $^{\circ}C$
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ²	150	mJ
I_{AR}	Avalanche Current ¹	34	A
E_{AR}	Repetitive Avalanche Energy ¹	15	mJ
dv/dt	Peak Diode Reverse Recovery ³	5.5	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}C$
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	9.3 (Typical)	

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.² $V_{DD} = 25V$, starting $T_J = 25^{\circ}C$, $L = 0.26mH$, Peak $I_L = 34A$, $V_{GS} = 10V$ ³ $I_{SD} \leq 34A$, $di/dt \leq 70A/\mu s$, $V_{DD} \leq 100V$, $T_J \leq 150^{\circ}C$

Device Characteristics

2 Device Characteristics

2.1 Electrical Characteristics

Table 3 Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 1.0mA$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.13	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1.0mA$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	70	$m\Omega$	$V_{GS} = 10V, I_{D2} = 21A^1$
		—	—	81		$V_{GS} = 10V, I_{D1} = 34A^1$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
G_{fs}	Forward Transconductance	9.0	—	—	S	$V_{DS} = 15V, I_{D2} = 21A$
I_{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	$V_{DS} = 80V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Leakage Reverse	—	—	-100		$V_{GS} = -20V$
Q_G	Total Gate Charge	—	—	125	nC	$I_{D1} = 34A$
Q_{GS}	Gate-to-Source Charge	—	—	22		$V_{DS} = 50V$
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	65		$V_{GS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	—	35	ns	$I_{D1} = 34A^{**}$ $V_{DD} = 50V$ $R_G = 2.35\Omega$ $V_{GS} = 10V$
t_r	Rise Time	—	—	190		
$t_{d(off)}$	Turn-Off Delay Time	—	—	170		
t_f	Fall Time	—	—	130		
$L_s + L_D$	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm/ 0.25 in from package) with Source wire internally bonded from Source pin to Drain pad
C_{iss}	Input Capacitance	—	3700	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0MHz$
C_{oss}	Output Capacitance	—	1100	—		
C_{rss}	Reverse Transfer Capacitance	—	200	—		
C_{DC}	Drain-to-Case Capacitance	—	12	—		

** Switching speed maximum limits are based on manufacturing test equipment and capability.

¹ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$

Device Characteristics

2.2 Source-Drain Diode Ratings and Characteristics

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	34	A	
I _{SM}	Pulsed Source Current (Body Diode) ¹	—	—	136	A	
V _{SD}	Diode Forward Voltage	—	—	1.8	V	T _J = 25°C, I _S = 34A, V _{GS} = 0V ²
t _{rr}	Reverse Recovery Time	—	—	500	ns	T _J = 25°C, I _F = 34A, V _{DD} ≤ 50V di/dt = 100A/μs
Q _{rr}	Reverse Recovery Charge	—	1.9	—	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Case	—	—	0.83	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Case-to-Sink	—	0.21	—	
$R_{\theta JA}$	Junction-to-Ambient (Typical socket mount)	—	—	48	

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.

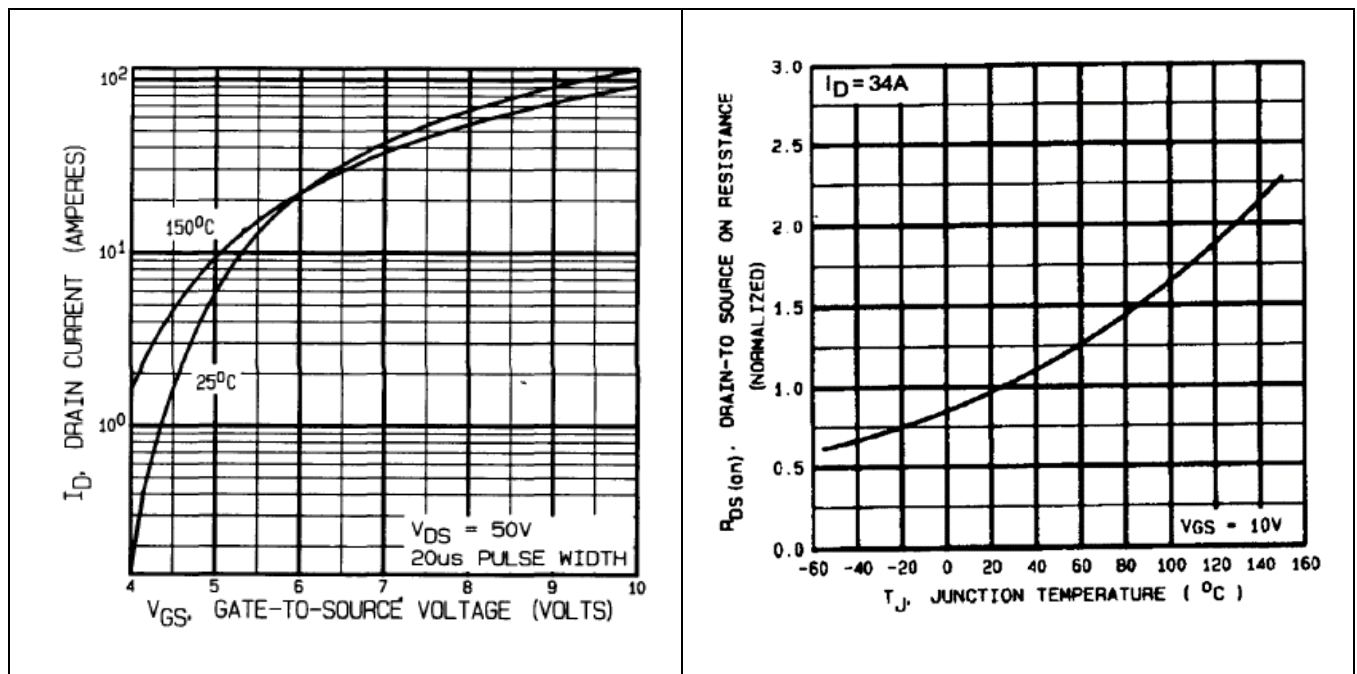
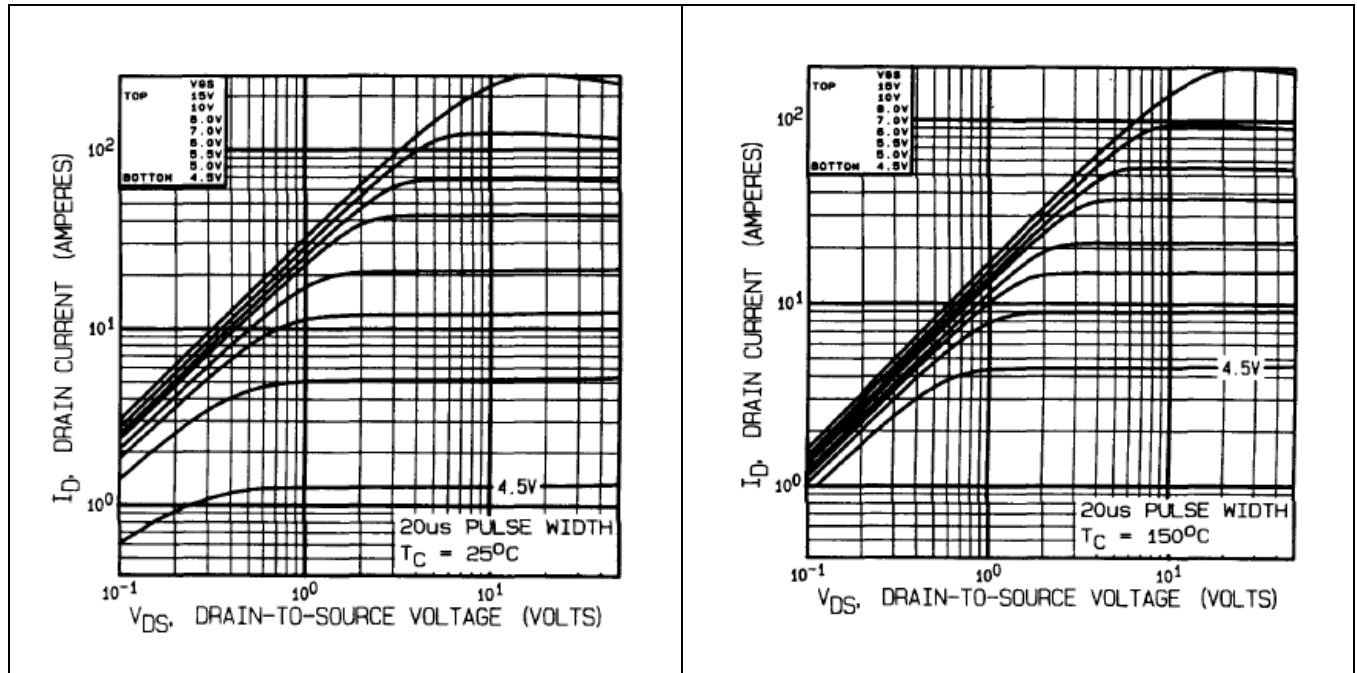
² Pulse width $\leq 300\ \mu\text{s}$; Duty Cycle $\leq 2\%$

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Power MOSFET Thru - Hole (TO-254AA)

Electrical Characteristics Curves

3 Electrical Characteristics Curves



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Electrical Characteristics Curves

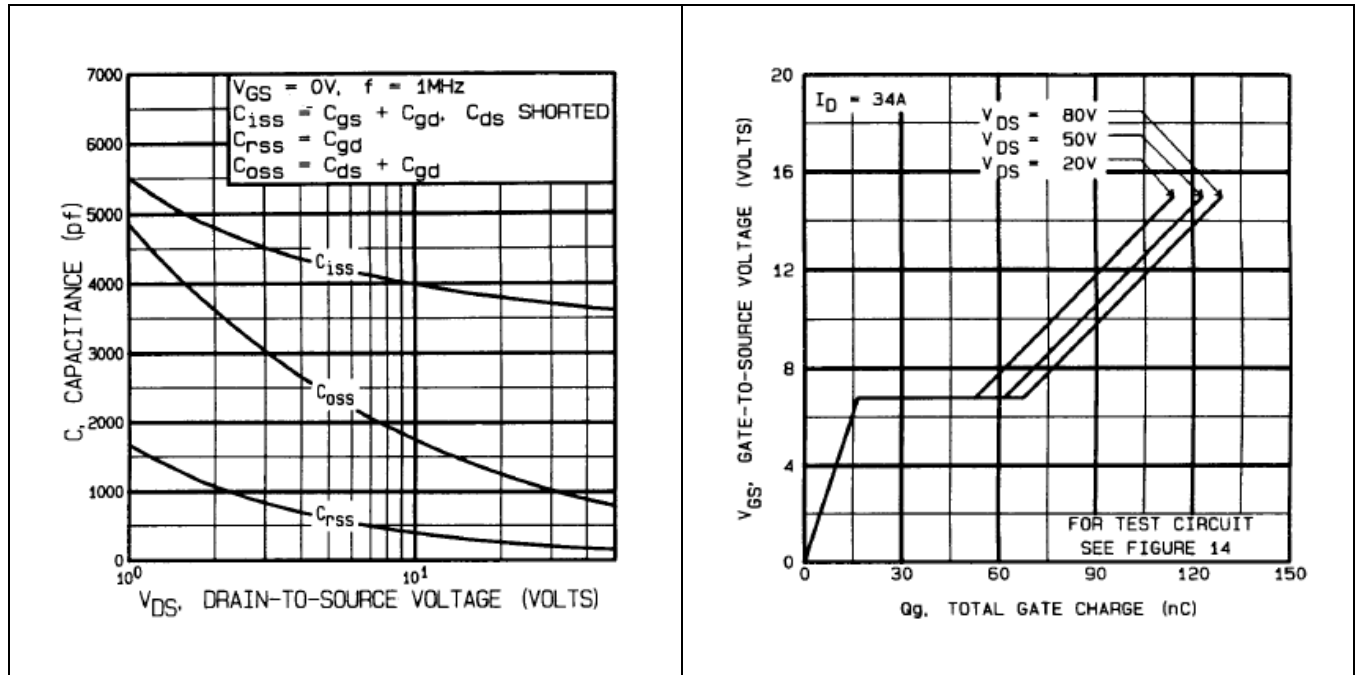


Figure 5 Typical Capacitance Vs. Drain-to-Source Voltage

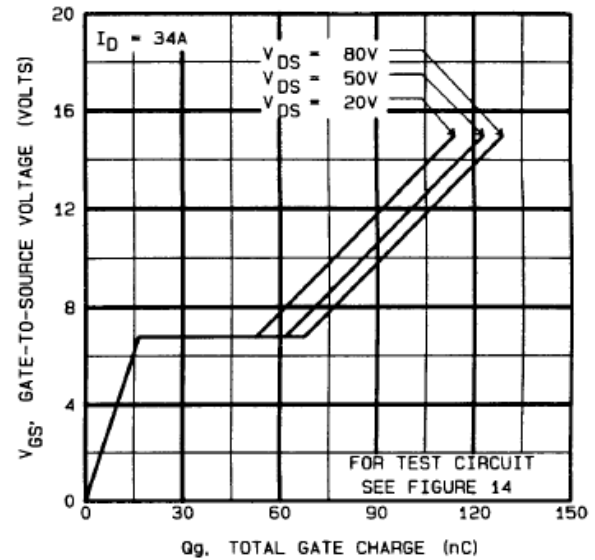


Figure 6 Typical Gate Charge Vs. Gate-to-Source Voltage

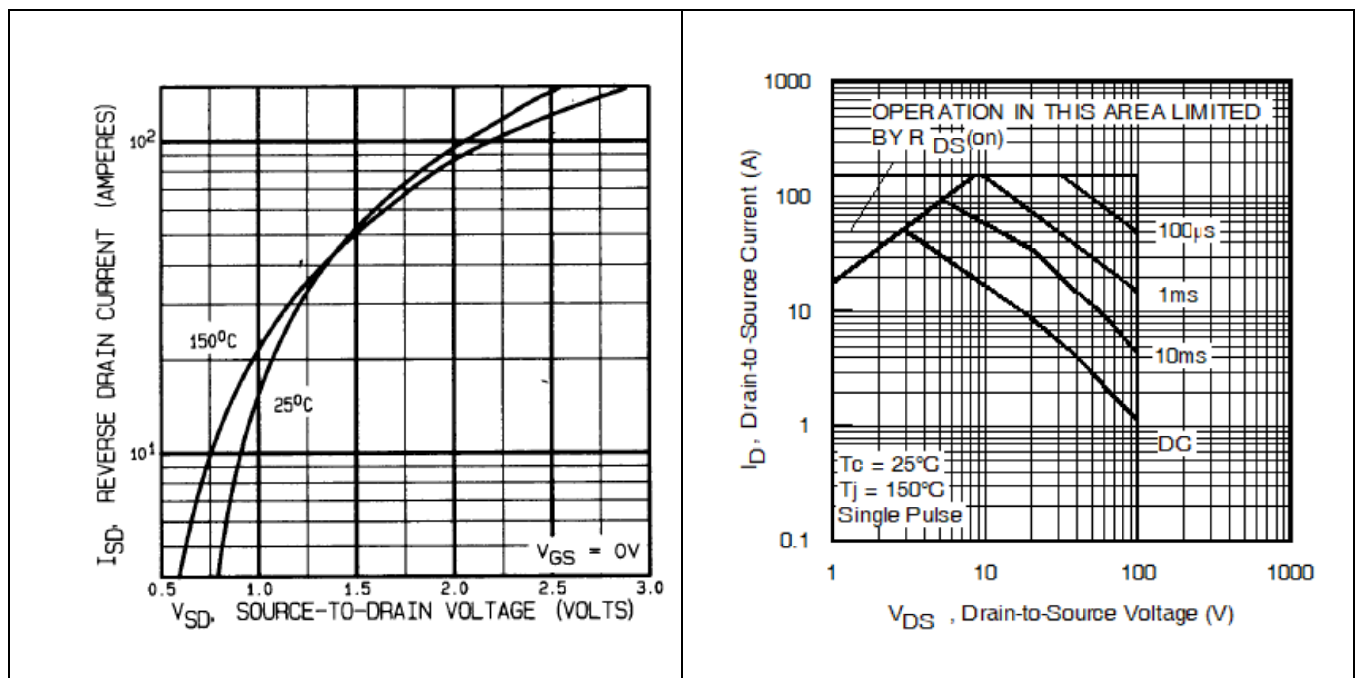


Figure 7 Typical Source-Drain Current Vs. Diode Forward Voltage

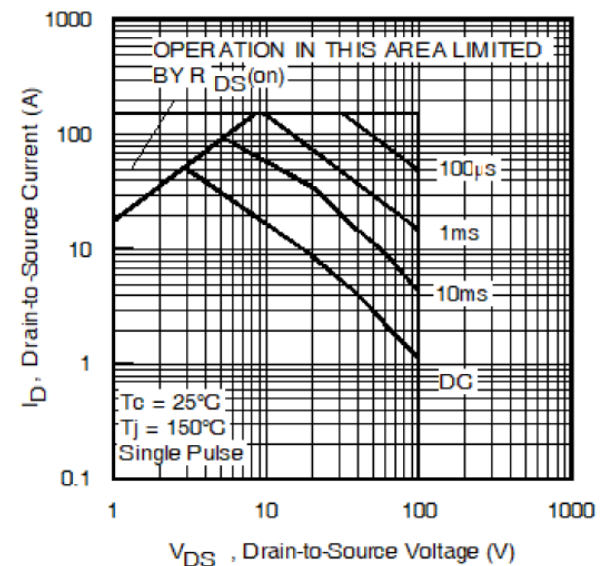


Figure 8 Maximum Safe Operating Area

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Electrical Characteristics Curves

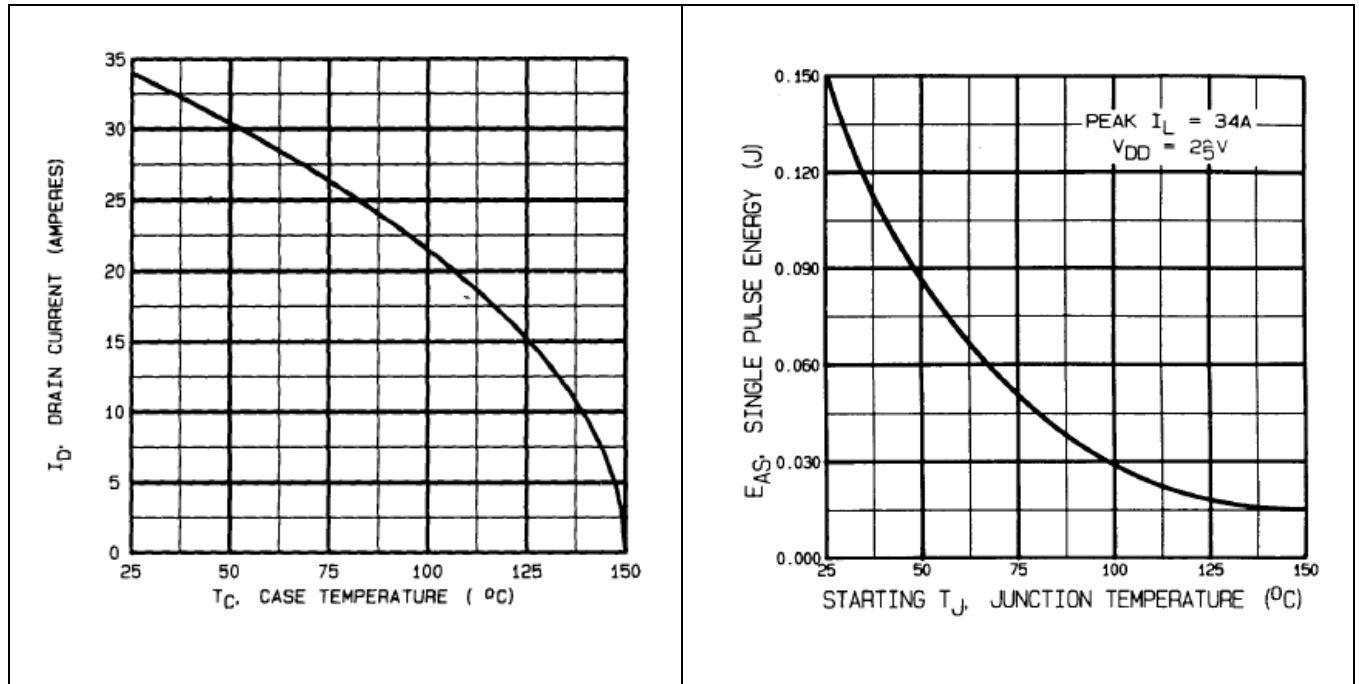


Figure 9 Maximum Drain Current Vs. Case Temperature

Figure 10 Maximum Avalanche Energy Vs. Junction Temperature

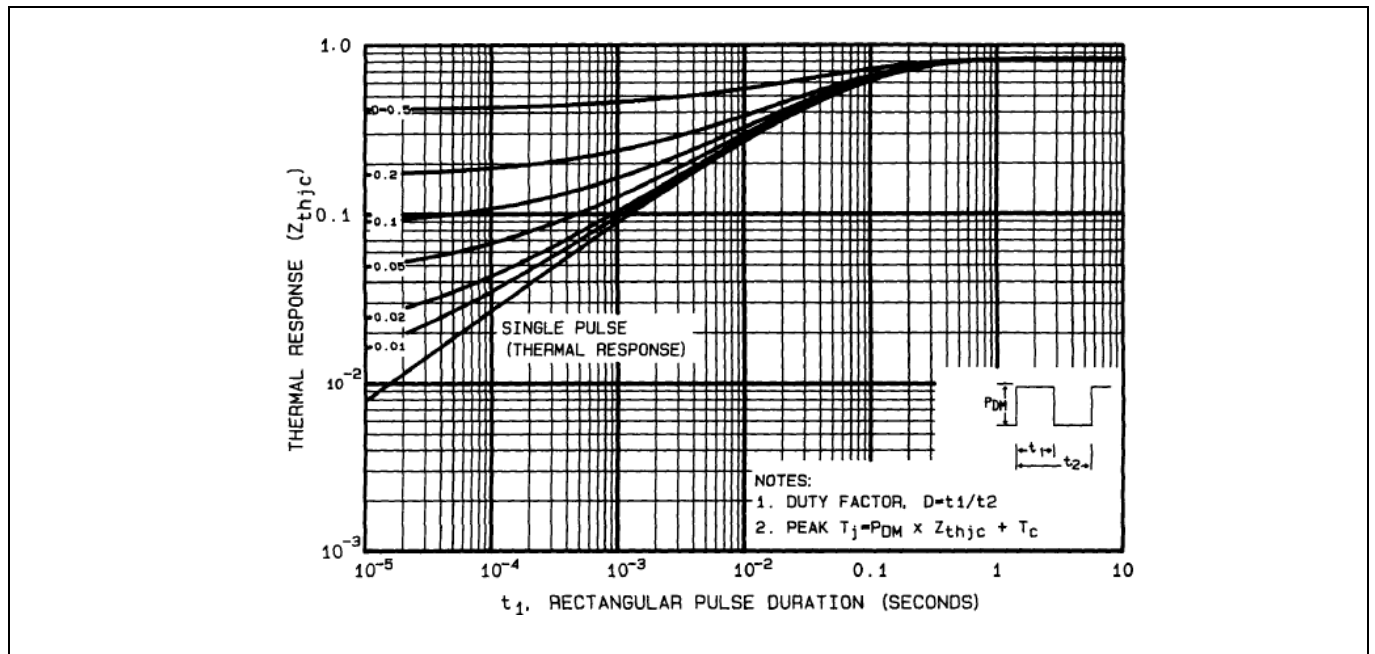


Figure 11 Maximum Effective Transient Thermal Impedance, Junction-to-Case

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Test Circuits

4 Test Circuits

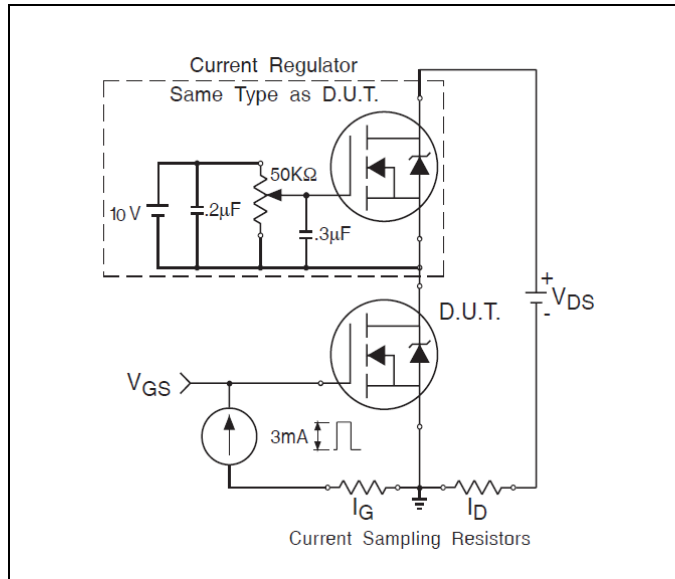


Figure 12 Gate Charge Test Circuit

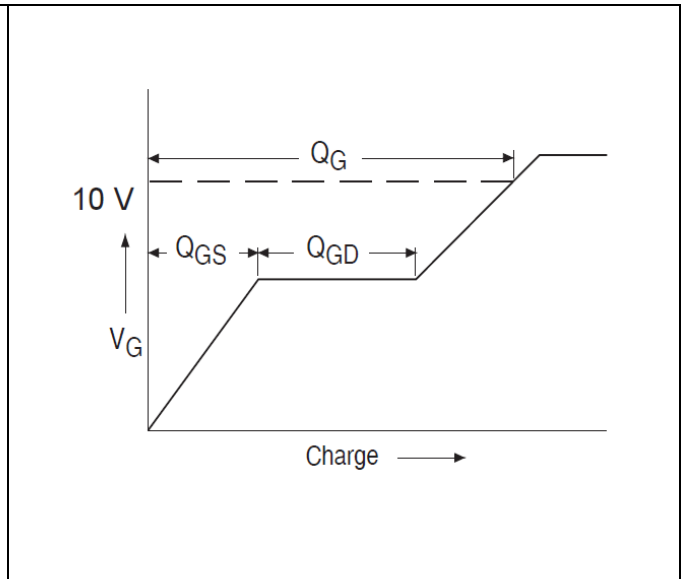


Figure 13 Gate Charge Waveform

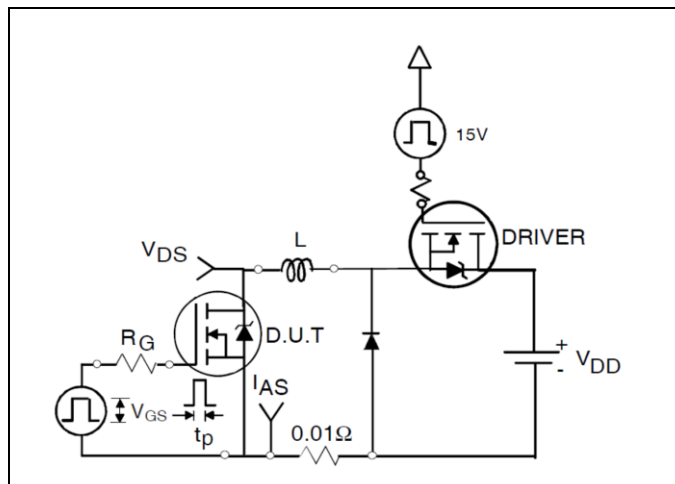


Figure 14 Unclamped Inductive Test Circuit

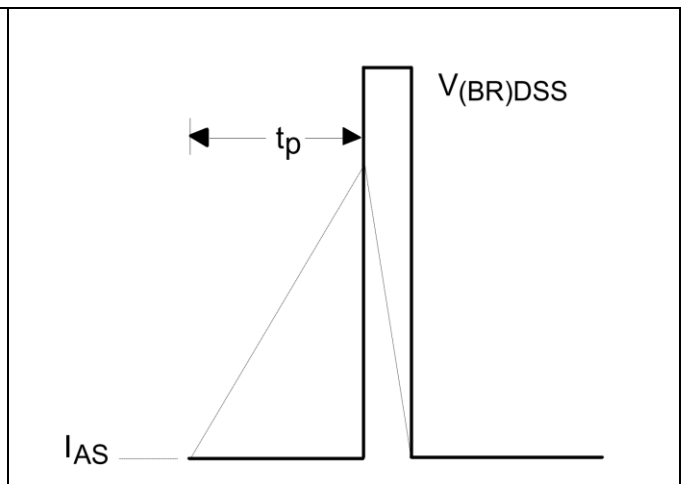


Figure 15 Unclamped Inductive Waveform

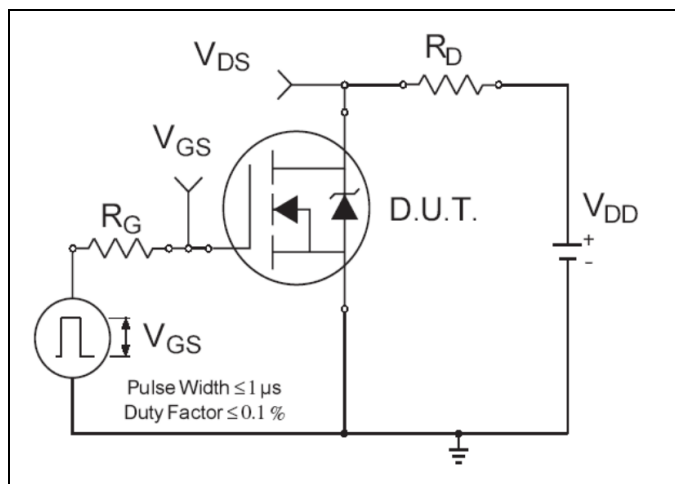


Figure 16 Switching Time Test Circuit

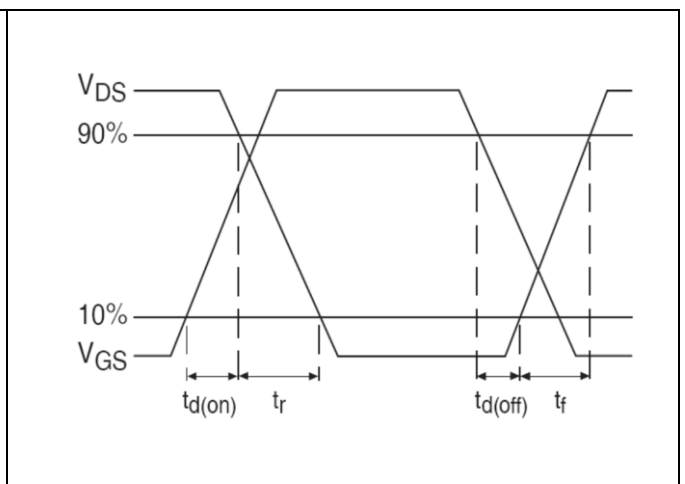


Figure 17 Switching Time Waveforms

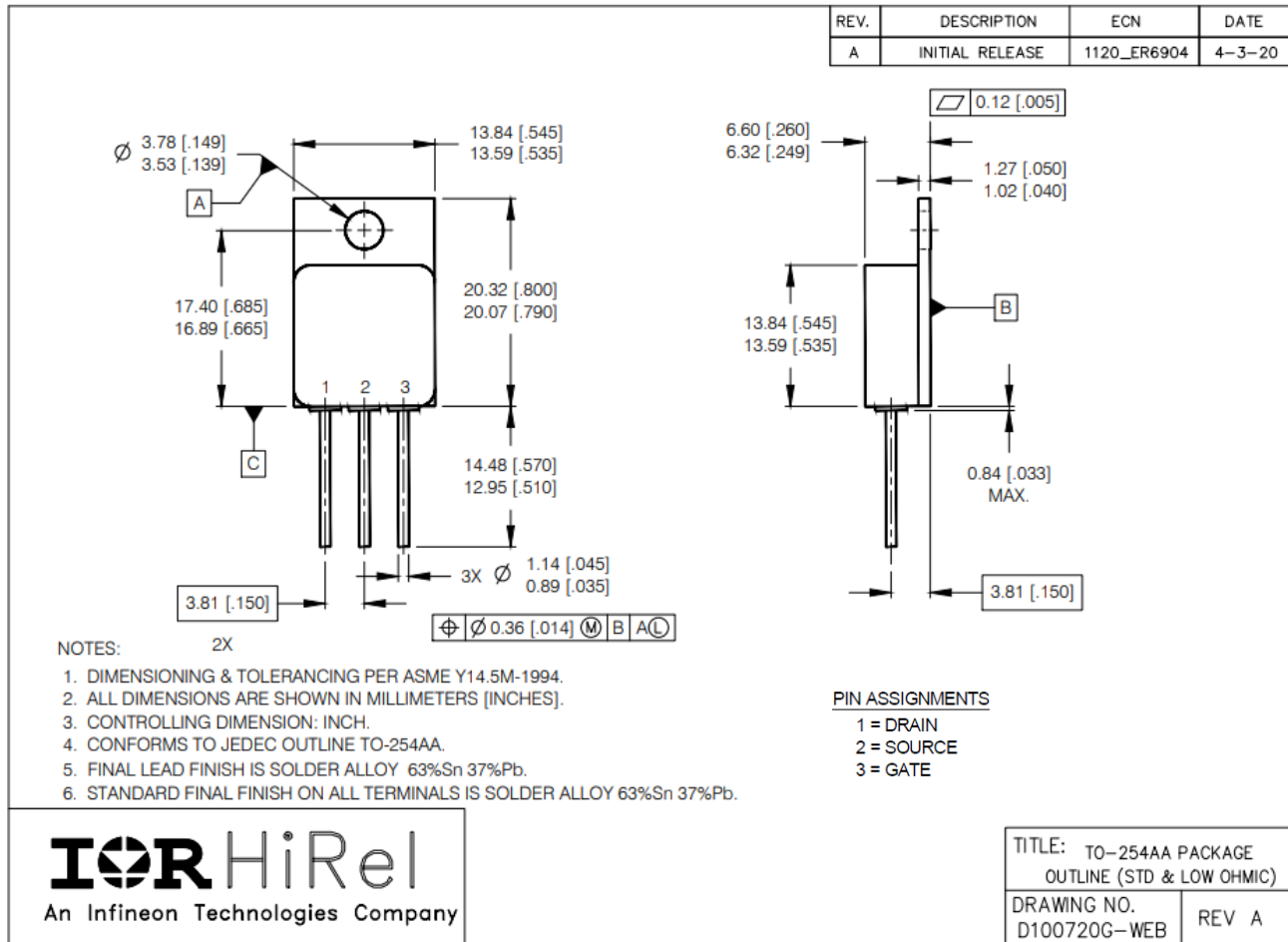
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Package Outline

5 Package Outline

Note: For the most updated package outline, please see the website: [TO-254AA](http://www.infineon.com/toc-254aa)



BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

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Revision history

Revision history

Document version	Date of release	Description of changes
Rev C	01/09/1990	Datasheet (PD-90487C)
Rev D	08/06/2024	Updated based on ECN-1120_10008

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